**WHAT IS CLAIMED IS:**

1. A photosensitive resin composition comprising an aromatic polyimide precursor, wherein a 10 μm thick polyimide film made from the resin composition by imidation ring closure and deposited on a silicon substrate has light transmittance at a wavelength of 365 nm of at least 1% and a residual stress of at most 25 MPa.

2. The photosensitive resin composition as claimed in claim 1, wherein the light transmittance at a wavelength of 365 nm is at least 5%.

3. The photosensitive resin composition as claimed in claim 1, wherein the aromatic polyimide precursor is soluble in an aqueous alkaline solution.

4. A method for forming patterns, which comprises applying a photosensitive resin composition onto a substrate and drying, exposing the composition, developing the composition, and heating the composition, wherein the composition comprises a photosensitive resin composition comprising an aromatic polyimide precursor wherein a 10 μm thick polyimide film made from the resin composition by imidation ring closure and deposited on a silicon substrate has light transmittance at a wavelength of 365 nm of at least 1% and a residual stress of at most 25 MPa.

5. The patterning method as claimed in claim 4, wherein i-lines are used as a light source in the step of exposing.

6. The patterning method as claimed in claim 5, wherein the substrate is a silicon wafer having a diameter of at least 12 inches.

7. An electronic component having a layer patterned according to the method of claim 4.

8. An electronic component as claimed in claim 7, wherein the component is a semiconductor device and the patterned layer is a surface-protecting film.

9. An electronic component as claimed in claim 7, wherein the patterned layer is an interlayer insulating film.